

< C band internally matched power GaAs FET > MGFC40V3742 3.7 – 4.2 GHz BAND / 10W

DESCRIPTION

The MGFC40V3742 is an internally impedance-matched GaAs power FET especially designed for use in 3.7 - 4.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

- Internally matched to 50(ohm) system
- High output power
- P1dB=10W (TYP.) @f=3.7 4.2GHz
- High power gain
- GLP=11.0dB (TYP.) @f=3.7 4.2GHz • High power added efficiency
- P.A.E.=32% (TYP.) @f=3.7 4.2GHz • Low distortion [item -51]
- IM3=-45dBc (Typ.) @Po=29.0dBm S.C.L

APPLICATION

- item 01 : 3.7 4.2 GHz band microwave high power amplifier
- item 51 : 3.7 4.2 GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

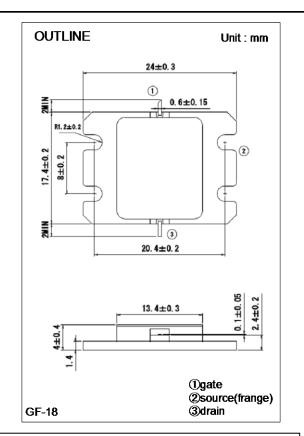
• VDS=10V • ID=2.4A • RG=50ohm Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

Parameter	Ratings	Unit
Gate to drain breakdown voltage	-15	V
Gate to source breakdown voltage	-15	V
Drain current	6	А
Reverse gate current	-20	mA
Forward gate current	42	mA
Total power dissipation	50	W
Cannel temperature	175	°C
Storage temperature	-65 to +175	°C
	Gate to drain breakdown voltage Gate to source breakdown voltage Drain current Reverse gate current Forward gate current Total power dissipation Cannel temperature	Gate to drain breakdown voltage-15Gate to source breakdown voltage-15Drain current6Reverse gate current-20Forward gate current42Total power dissipation50Cannel temperature175Storage temperature-65 to +175

*1 : Tc=25°C

Electrical characteristics (Ta=25°C)



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Symbol	Parameter	Test conditions		Limits		
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	4.5	6	А
gm	Trans conductance	VDS=3V, ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=40mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A	39.5	40.5	-	dBm
GLP *2	Linear Power Gain	f=3.7 – 4.2GHz	10	11	-	dB
P.A.E.	Power added efficiency	Pin=22dBm *2	-	32	-	%
ID	Drain current		-	2.4	-	А
IM3 *3	3rd order IM distortion	7	-42	-45-	-	dBc
Rth(ch-c) *4	Thermal resistance	delta Vf method	-	-	3.5	°C/W

*3 :item -51, 2 tone test,Po=29.0dBm Single Carrier Level ,f=4.2GHz,delta f=10MHz

*4 :Channel-case

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